



DESCRIPTION:

The products are transistor opto-couplers in a plastic SOP4 package. The device combines an AlGaAs infrared emitting diode as the emitter which is optically coupled to a silicon planar phototransistor detector. With the robust coplanar double mold structure, the device provides the most stable isolation feature. The products are widely used in switch mode power supplies, programmable controllers, household appliances and office equipment.

MAIN FEATURES

High isolation 3750 VRMS

Operating temperature range -55°C to 125°C

RoHS & REACH Compliance

HBM: H3A; MM: M4; CDM:C3

CQC approved

VDE approved

UL approved

1

ABSOLUTE MAXIMUM RATINGS (Temperature=25°C)

Input	Forward Current	I_F	50	mA
	Peak Forward Current	I_{FP}	1	A
	Reverse Voltage	V_R	6	V
	Power Dissipation	P_D	75	mW
Output	Collector-emitter Voltage	V_{CEO}	80	V
	Emitter-collector Voltage	V_{ECO}	7	V
	Collector Current	I_C	50	mA
	Power Dissipation	P_C	150	mW
Total Power Dissipation		P_{tot}	225	mW
Isolation Voltage		V_{iso}	3750	Vrms
Operating Temperature		T_{opr}	-55~+125	
Junction Temperature		T_j	135	
Storage Temperature		T_{stg}	-55~+125	



Soldering Temperature	T_{sol}	260	
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NOTE1 μ

NOTE2

ELECTRICAL CHARACTERISTICS (Temperature=25°C)

Input	Forward Voltage	V_F	$I_F=10mA$	-	1.2	1.5	V
	Reverse Current	I_R	$V_R=6V$	-	-	1	μA
	Terminal Capacitance	C_t	$V=0,$ $f=1MHz$	-	10	-	pF
Output	Collector-Emitter dark current	I_{CEO}	$V_{CE}=20V,$ $I_F=0$	-	-	100	nA
	Collector-Emitter breakdown voltage	BV_{CEO}	$I_C=0.1mA$ $I_F=0$	80	-	-	V
	Emitter-Collector breakdown voltage	BV_{ECO}	$I_E=0.1mA$ $I_F=0$	7	-	-	V
Transfer Characteristics	Current transfer ratio	CTR	$I_F=5mA$ $V_{CE}=5V$	100	-	400	%
	Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_F=20mA$ $I_C=1mA$	-	0.06	0.2	V
	Isolation resistance	R_{IO}	DC500V 40~60%R.H.	10^{12}	10^{14}	-	Ω
	Floating Capacitance	C_{IO}	$V=0,$ $f=1MHz$	-	0.4	1	pF
	Cut-off Frequency	f_c	$V_{CE}=5V,$ $I_C=2mA$ $R_L=100\Omega,$ -3dB	-	80	-	kHz
	Rise Time	t_r	$V_{CE}=2V,$ $I_C=2mA$ $R_L=100\Omega$	-	3	18	μs
	Fall Time	t_f		-	4	18	μs
	Response Time	t_{on}		-	6	25	μs
		t_{off}		-	5	25	μs

NOTE1

P	200	400	$I_F=0.5mA, V_{CE}=5V$
	200	400	$I_F=5mA, V_{CE}=5V$
Q	100	300	$I_F=0.5mA, V_{CE}=5V$
	100	300	$I_F=5mA, V_{CE}=5V$



ORDERING INFORMATION

J	OC	T	357	P	t	-M4	/
JieJie Microelectronics Co., Ltd.	Opto Coupler	Transistor		CTR Rank:P/Q	t: High Temperature	SOP4	None:T1 R:T2
			Marketization Model				

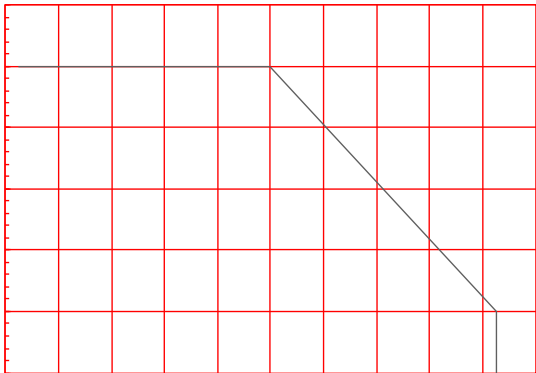
P Š P q T e m p e p r e F

MARKING

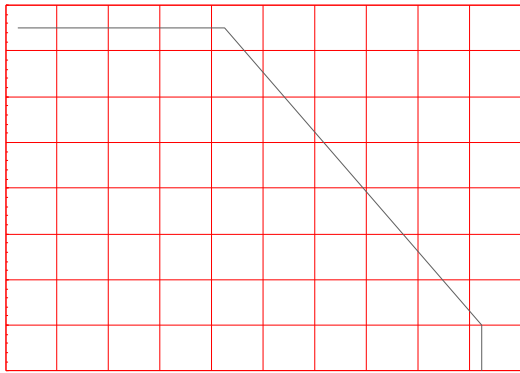


Characteristics Curves

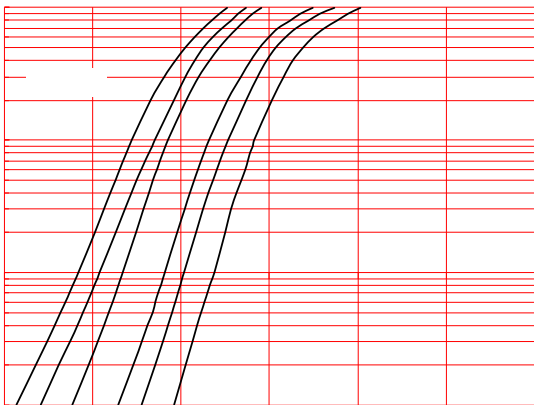
Max. Allowable LED Forward Current vs. Ambient Temperature



Collector Power Dissipation vs. Ambient Temperature



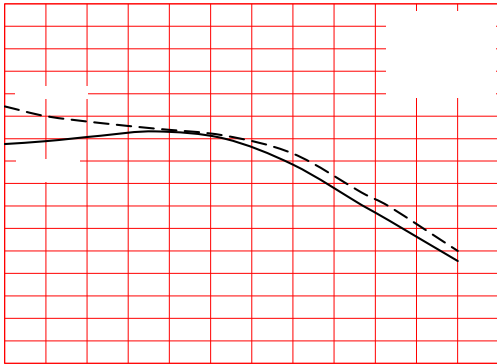
Forward Current vs. Forward Voltage



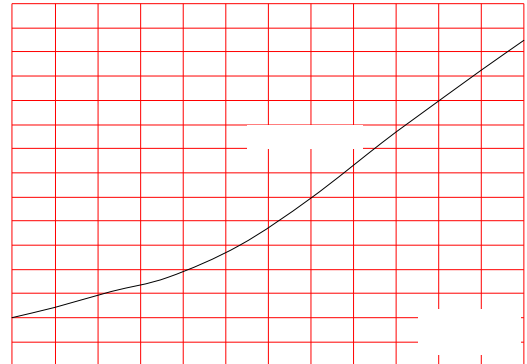
Normalized Collector Dark Current vs. Ambient Temperature



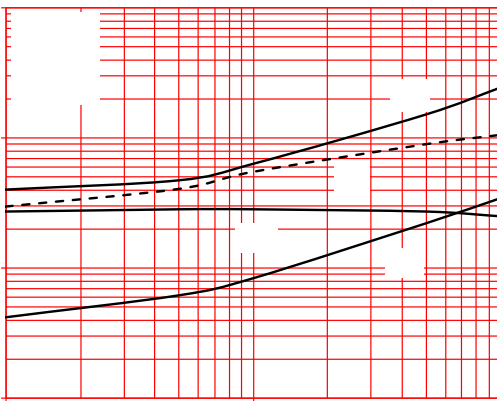
Normalized Current Transfer Ratio vs.
Ambient Temperature



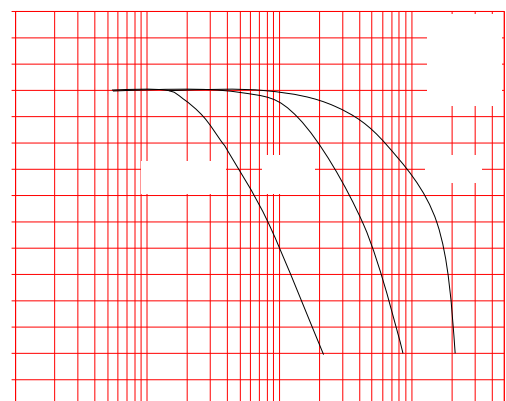
Normalized Collector-emitter Saturation
Voltage vs. Ambient Temperature



Response Time vs. Load Resistance

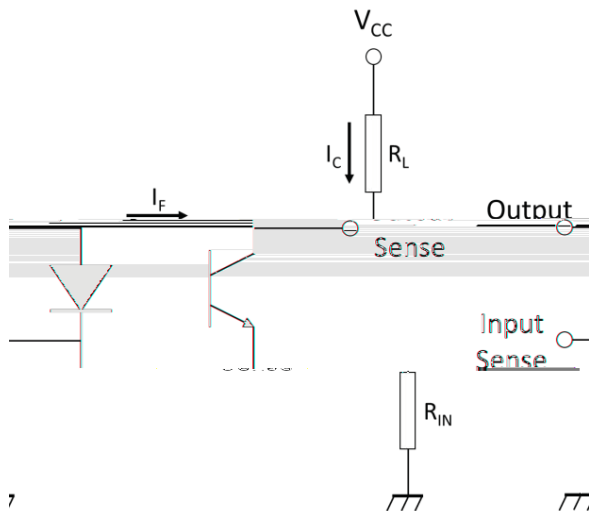


Frequency Response

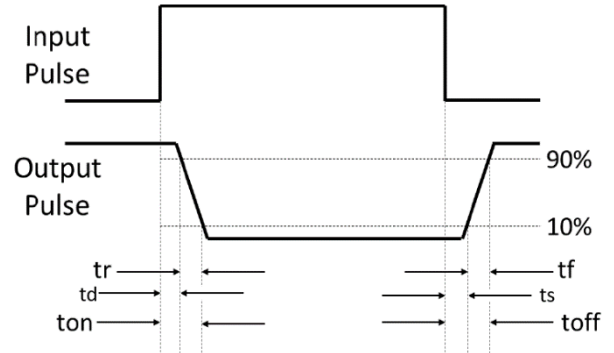


Test Circuits

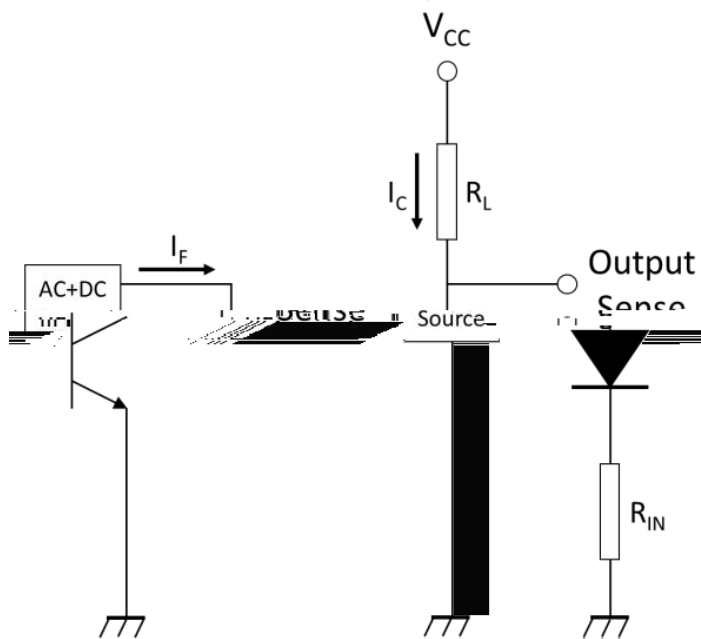
Test Circuits of Response Time



Curves of Response Time

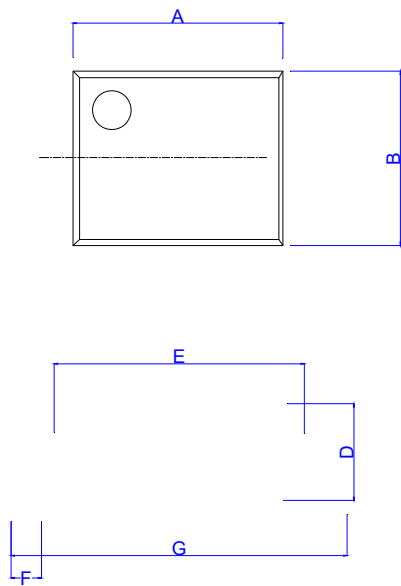


Test Circuits of Frequency Response





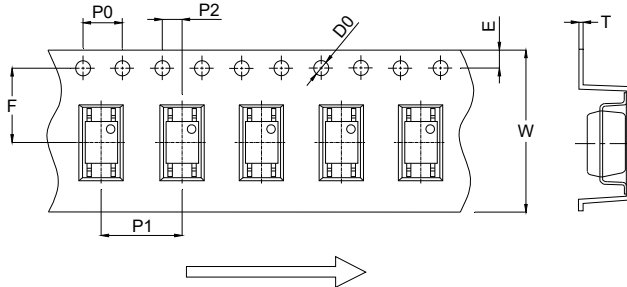
Package Dimension (Unit: mm)



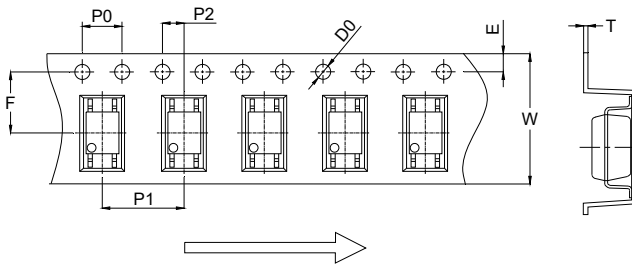
Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.40		4.80	0.173		0.189
B	3.60		4.20	0.142		0.165
C						
D	1.90		2.30	0.075		0.091
E	5.00		5.60	0.197		0.220
F						
G	6.70			0.264		
H						
I						
J						



CARRIER TAPE SPECIFICATIONS (Dimensions in mm unless otherwise stated)



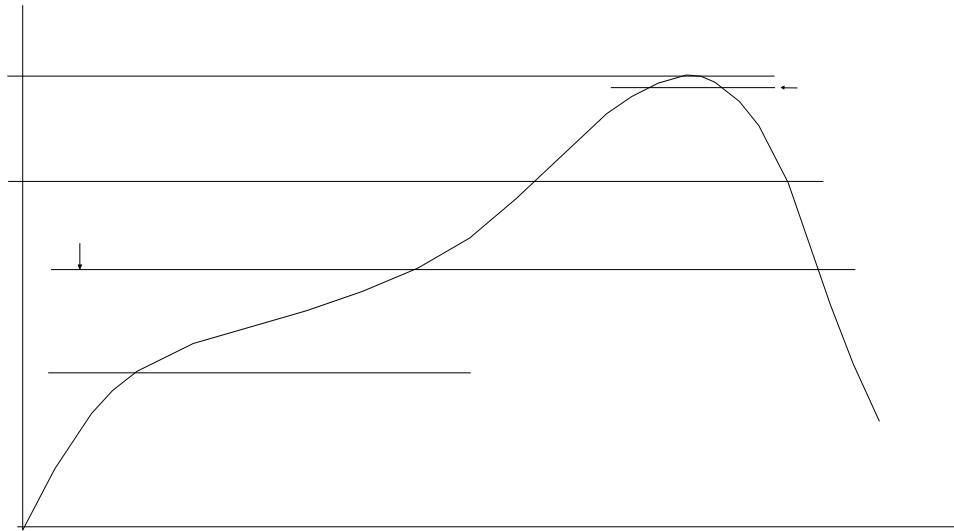
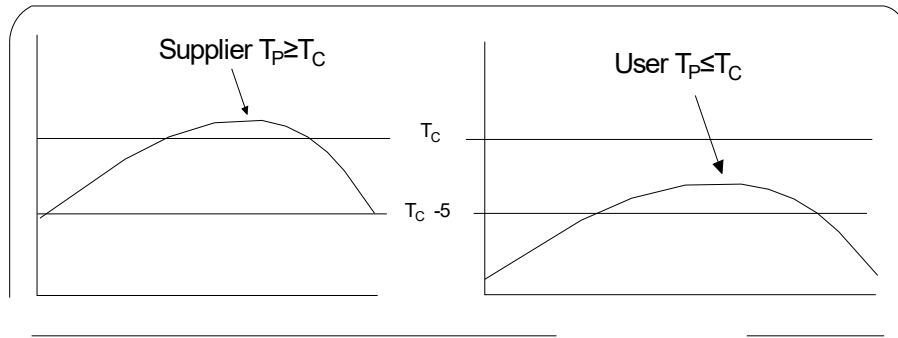
Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
D0		1.50	1.60		0.059	0.063
P0	3.90	4.00	4.10	0.154	0.157	0.161
P1	7.90	8.00	8.10	0.311	0.315	0.319
P2	1.90	2.00	2.10	0.075	0.079	0.083
E	1.65	1.75	1.85	0.065	0.069	0.073
F	7.40	7.50	7.60	0.291	0.295	0.299
T	0.27	0.30	0.33	0.011	0.012	0.013
W	15.80	16.00	16.20	0.622	0.630	0.638



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
D0		1.50	1.60		0.059	0.063
P0	3.90	4.00	4.10	0.154	0.157	0.161
P1	7.90	8.00	8.10	0.311	0.315	0.319
P2	1.90	2.00	2.10	0.075	0.079	0.083
E	1.65	1.75	1.85	0.065	0.069	0.073
F	4.40	4.50	4.60	0.173	0.177	0.181
T	0.25	0.30	0.35	0.010	0.012	0.014
W	11.90	12.00	12.30	0.469	0.472	0.484



REFLOW INFORMATION





Note:

1. Reflow soldering is recommended at the temperatures and times shown, no more than three times.
2. Avoid direct contact between the epoxy body and any tools or surfaces exceeding its maximum storage temperature.
3. Application of pressure on the epoxy body is prohibited at elevated temperatures. In specific scenarios, any applied force must not exceed 2.5N.
4. Ensure the component has cooled to ambient temperature before proceeding with any subsequent manufacturing steps.
5. The component has a shelf lif